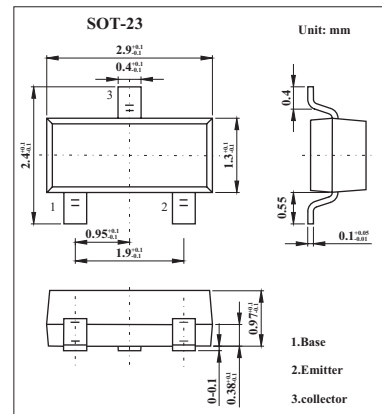


MMBTA42

■ Features

- NPN Silicon



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V _{CEO}	300	V
Collector-base voltage	V _{CB0}	300	V
Emitter-base voltage	V _{EB0}	6	V
Collector current-continuous	I _C	500	mA
Total device dissipation FR-5 board *1			
@TA = 25°C	P _D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal resistance, junction-to-ambient	R _{θJA}	556	°C/W
Total device dissipation alumina substrate *2			
@TA = 25°C	P _D	300	mW
derate above 25°C		2.4	mW/°C
Thermal resistance, junction-to-ambient	R _{θJA}	417	°C/W
Junction and storage temperature	T _J , T _{stg}	-55 to +150	°C

* 1. FR-5 = 1.0 X 0.75 X 0.062 in.

* 2. Alumina = 0.4 X 0.3 X 0.024 in. 99.5% alumina.

Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-emitter breakdown voltage*	$V_{(BR)CEO}$	$I_C = 1.0\text{ mA}, I_B = 0$	300			V
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\ \mu\text{A}, I_E = 0$	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\ \mu\text{A}, I_C = 0$	6			V
Collector cutoff current	I_{CBO}	$V_{CB} = 200\text{ V}, I_E = 0$			0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 6.0\text{ V}, I_C = 0$			0.1	μA
DC current gain *	h_{FE}	$I_C = 1.0\text{ mA}, V_{CE} = 10\text{ V}$	25			
		$I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$	40			
		$I_C = 30\text{ mA}, V_{CE} = 10\text{ V}$	40			
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = 20\text{ mA}, I_B = 2.0\text{ mA}$			0.5	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	$I_C = 20\text{ mA}, I_B = 2.0\text{ mA}$			0.9	V
Current-gain - bandwidth product	f_T	$I_C = 10\text{ mA}, V_{CE} = 20\text{ V}, f = 100\text{ MHz}$	50			MHz
Collector-base capacitance	C_{cb}	$V_{CB} = 20\text{ V}, I_E = 0, f = 1.0\text{ MHz}$			3	pF

* Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

Marking

Marking	1D
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